CMSD2836 CMSD2838

SUPERmini™ DUAL SILICON SWITCHING DIODE



The following configurations are available:



DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD2836 and CMSD2838 types are ultra-high speed silicon switching diodes manufactured by the epitaxial planar process, in an epoxy molded SUPERmini™ surface mount package, designed for high speed switching applications.

CMSD2836 DUAL, COMMOM ANNODE MARKING CODE: A2C CMSD2838 DUAL, COMMON CATHODE MARKING CODE: A6C

MAXIMUM RATINGS: $(T_A = 25^{\circ}C)$

SYMBOL		UNITS
V_{RRM}	75	V
IO	200	mA
I _{FM}	300	mA
P_{D}	250	mW
T_J, T_stg	-65 to +150	°C
$\Theta_{\sf JA}$	500	°C/W
	V _{RRM} I _O I _{FM} P _D T _J ,T _{stg}	V _{RRM} 75 I _O 200 I _{FM} 300 P _D 250 T _J ,T _{stg} -65 to +150

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
B_{VR}	I _R =100μA	75			V
I_{R}	V _R =50V			100	nA
V_{F}	I _F =10mA			1.0	V
V_{F}	I _F =50mA			1.0	V
V_{F}	I _F =100mA			1.2	V
C_T	V _R =0, f=1 MHz		1.5	4.0	pF
t _{rr}	$I_R=I_F=10$ mA, $R_L=100\Omega$, Rec. to 1.0mA			4.0	ns

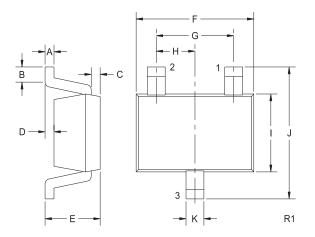
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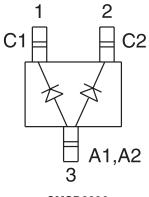
SOT-323 CASE - MECHANICAL OUTLINE



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	0.004	0.008	0.10	0.20			
В	0.004	-	0.10	-			
С	0.004	0.008	0.10	0.20			
D	-	0.004	_	0.10			
E	0.031	0.043	0.80	1.10			
F	0.071	0.087	1.80	2.20			
G	0.051		1.30				
Н	0.026		0.65				
	0.045	0.053	1.15	1.35			
J	0.079	0.087	2.00	2.20			
K	0.008	0.016	0.20	0.40			

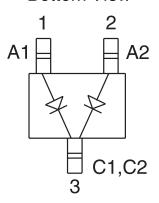
SOT-323 (REV: R1)





CMSD2836

Bottom View



CMSD2838